Claims:

1. A copper alloy bonding wire for semiconductor manufactured by wire drawing of a copper alloy, wherein said copper alloy ~~essentially~~ consists of 0.13 to 1.15% by mass of Pd, ~~optionally at least one of Ag and Au in a total amount of 0.0005 to 0.07% by mass, further optionally at least one of Ti: 0.0005 to 0.01% by mass, B: 0.0005 to 0.007% by mass and P: 0.0005 to 0.02% by mass, in a total amount of 0.0005 to 0.025% by mass,~~ and a remainder ~~comprised~~ consisting of copper.

2. The copper alloy bonding wire for semiconductor according to claim 1, comprising crystal grains not smaller than 2μm and not larger than 75μm on average, said crystal grains being observed on a wire cross-section surface parallel to a wire longitudinal direction.

3. A copper alloy bonding wire for semiconductor manufactured by wire drawing of a copper alloy, wherein said copper alloy consists of 0.13 to 1.15% by mass of Pd, at least one of Ag and Au in a total amount of 0.0005 to 0.07% by mass, and a remainder consisting of copper.

4. The copper alloy bonding wire for semiconductor according to claim 3, comprising crystal grains not smaller than 2μm and not larger than 75μm on average, said crystal grains being observed on a wire cross-section surface parallel to a wire longitudinal direction.

5. A copper alloy bonding wire for semiconductor manufactured by wire drawing of a copper alloy, wherein said copper alloy consists of more than 0.5% and not more than 1.15% by mass of Pd, at least one of Ti: 0.0005 to 0.01% by mass, B: 0.0005 to 0.007% by mass and P: 0.0005 to 0.02% by mass, in a total amount of 0.0005 to 0.025% by mass, and a remainder consisting of copper.

6. The copper alloy bonding wire for semiconductor according to claim 5, comprising crystal grains not smaller than 2μm and not larger than 75μm on average, said crystal grains being observed on a wire cross-section surface parallel to a wire longitudinal direction.

7. A copper alloy bonding wire for semiconductor manufactured by wire drawing of a copper alloy, wherein said copper alloy consists of more than 0.5% and not more than 1.15% by mass of Pd, at least one of Ag and Au in a total amount of 0.0005 to 0.07% by mass, at least one of Ti: 0.0005 to 0.01% by mass, B: 0.0005 to 0.007% by mass and P: 0.0005 to 0.02% by mass, in a total amount of 0.0005 to 0.025% by mass, and a remainder consisting of copper.

8. The copper alloy bonding wire for semiconductor according to claim 7, comprising crystal grains not smaller than 2μm and not larger than 75μm on average, said crystal grains being observed on a wire cross-section surface parallel to a wire longitudinal direction.